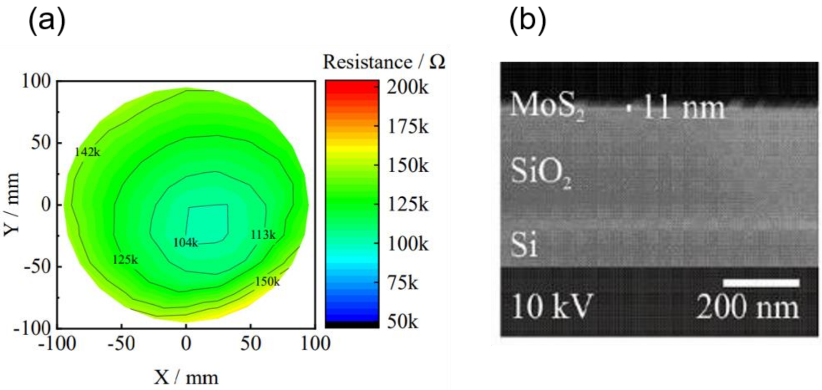

Figure 1. a) 8" wafer homogeneity for the resistance of the MoS_2 layer on SiO_x / Si grown by ALD. b) Cross-sectional SEM image of the MoS_2 deposited on 8" SiO_x/Si wafers.[1,2]

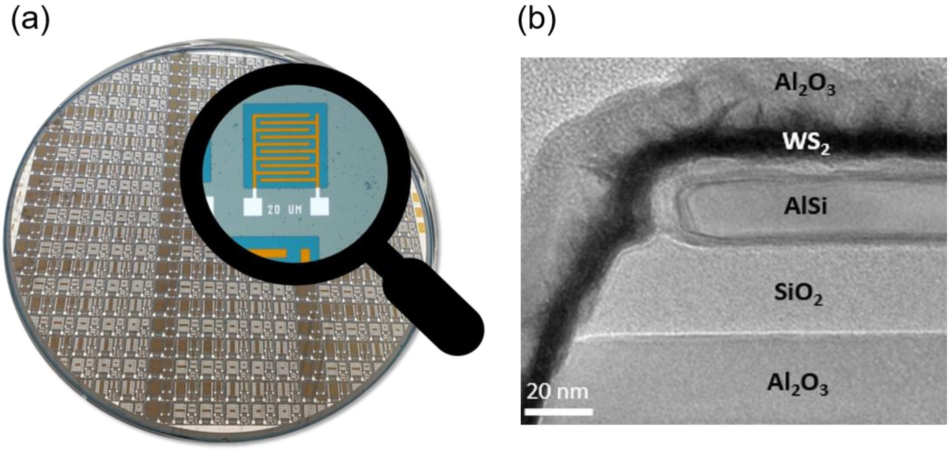

Figure 2. a) Top and microscopic view of WS_2 grown by ALD and patterned on IDE structures.[4] b) Cross-sectional TEM image of the WS_2 patterned on IDEs with protective Al_2O_3 capping layer.[4]

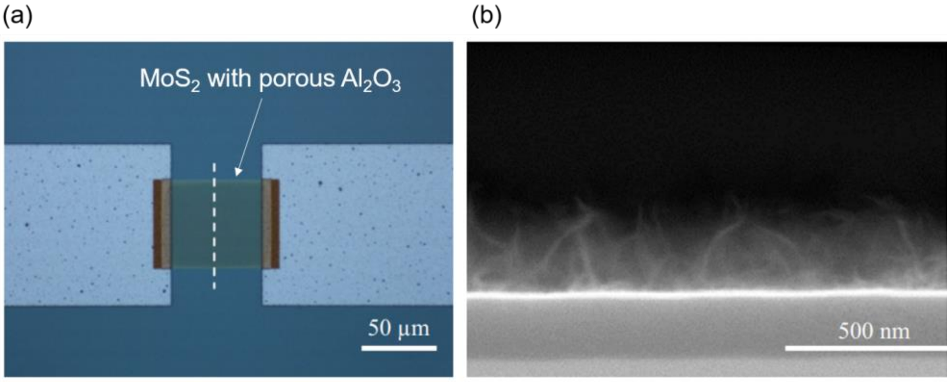

Figure 3. a) Microscopic image of structured MoS_2 between AlSi electrodes with porous Al_2O_3 capping layer.[2,3] b) Cross-sectional SEM image of the MoS_2 with porous Al_2O_3 capping layer.[2,3]

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